NSR15SDW1T1 NSR15SDW1T2

Dual RF Schottky Diode

These diodes are designed for analog and digital applications, including DC based signal detection and mixing applications.

Features

- Low Capacitance (<1 pF)
- Low V_F (390 mV typical @ 1 mA)
- Low $V_{F\Delta}$ (1 mV typical @ 1 mA)
- Pins 2 and 5 Shorted
- Pb–Free Packages are Available

Benefits

- Reduced Parasitic Losses
- Accurate Signal Measurement
- Reduced Cross Talk

MAXIMUM RATINGS

Rating	Symbol	Max	Unit	
Peak Reverse Voltage	V _R	15	V	
Forward Current	١ _F	30	mA	
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C	
ESD Rating: Class 1 per Human Body Model Class A per Machine Model				

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance Junction-to-Ambient	$R_{ hetaJA}$	500	°C/W

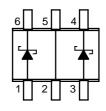
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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RF SCHOTTKY BARRIER DIODES 15 VOLTS, 30 mA





MARKING DIAGRAM



R6 = Specific Device Code M = Date Code = Pb-Free Package (Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping †
NSR15SDW1T1	SC-88	3000/Tape & Reel
NSR15SDW1T1G	SC-88 (Pb-Free)	3000/Tape & Reel
NSR15SDW1T2	SC-88	3000/Tape & Reel
NSR15SDW1T2G	SC-88 (Pb-Free)	3000/Tape & Reel
NSR15SDW1T4	SC-88	10,000/Tape & Reel
NSR15SDW1T4G	SC-88 (Pb-Free)	10,000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSR15SDW1T1 NSR15SDW1T2

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Breakdown Voltage (I _R = 10 μ A)	V _{BR}	15	20	-	V
Reverse Leakage (V _R = 1 V)	I _R	-	2	50	nA
Forward Voltage (I _F = 1 mA)	V _{F1}	-	390	415	mV
Forward Voltage (I _F = 10 mA)	V _{F2}	-	530	680	mV
Delta V _F (I _F = 1 mA, All Diodes)	ΔV_{F}	-	1	15	mV
Capacitance ($V_F = 0 V$, f = 1 MHz)	CT	_	0.8	1	pF

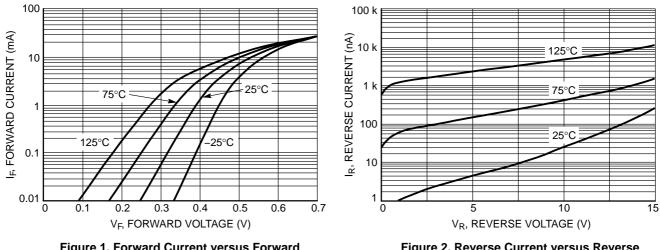


Figure 1. Forward Current versus Forward Voltage at Temperatures

Figure 2. Reverse Current versus Reverse Voltage

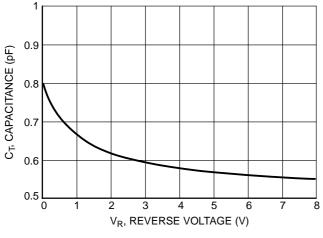


Figure 3. Total Capacitance versus Reverse Voltage

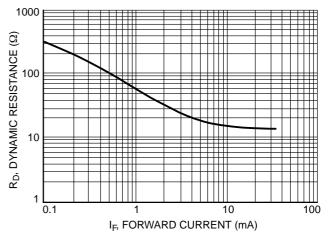


Figure 4. Dynamic Resistance versus Forward Current

NSR15SDW1T1 NSR15SDW1T2

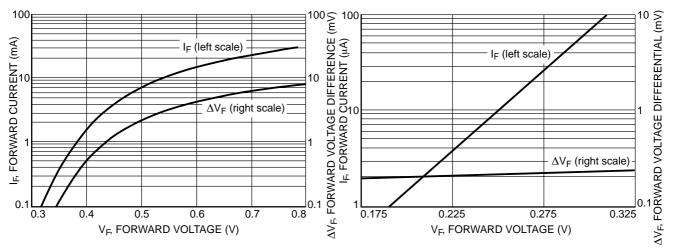
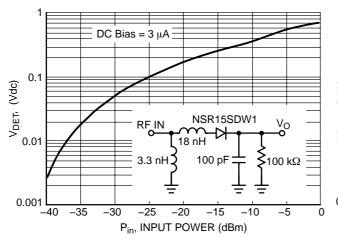


Figure 5. Typical V_F Match at Mixer Bias Levels

Figure 6. Typical V_F Match at Detector Bias Levels



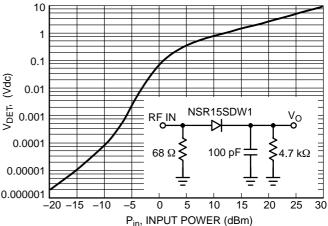




Figure 8. Typical Output Voltage versus Input Power, Large Signal Detector Operating at 915 MHz

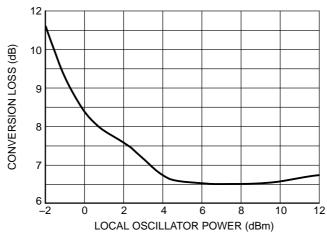
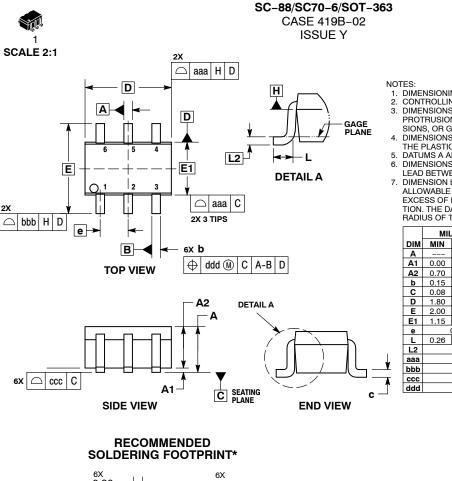


Figure 9. Typical Conversion Loss versus L.O. Drive, 2.0 GHz

)nsemi

DATE 11 DEC 2012



6X 0.30 0.66 2 50 0.65 PITCH DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION MILLIMETERS
- CONTROLLING DIMENSION: MILLIMETERS. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRU-SIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. SIONS, OH GATE BUHHS SHALL NOT EXCEED 0.20 PEH END. DIMENSIONS D AND ET AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H. DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS 5 AND 6 APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
Е	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е	(0.65 BS	С	0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10				0.004	

GENERIC **MARKING DIAGRAM***



XXX = Specific Device Code

- М = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y

DATE 11 DEC 2012

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13:	STYLE 14:	STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:
PIN 1. ANODE	PIN 1. VREF	PIN 1. ANODE 1	PIN 1. BASE 1	PIN 1. BASE 1	PIN 1. VIN1
2. N/C	2. GND	2. ANODE 2	2. EMITTER 2	2. EMITTER 1	2. VCC
3. COLLECTOR	3. GND	3. ANODE 3	3. COLLECTOR 2	3. COLLECTOR 2	3. VOUT2
4. EMITTER	4. IOUT	4. CATHODE 3	4. BASE 2	4. BASE 2	4. VIN2
5. BASE	5. VEN	5. CATHODE 2	5. EMITTER 1	5. EMITTER 2	5. GND
6. CATHODE	6. VCC	6. CATHODE 1	6. COLLECTOR 1	6. COLLECTOR 1	6. VOUT1
STYLE 19:	STYLE 20:	STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:
PIN 1. I OUT	PIN 1. COLLECTOR	PIN 1. ANODE 1	PIN 1. D1 (i)	PIN 1. Vn	PIN 1. CATHODE
2. GND	2. COLLECTOR	2. N/C	2. GND	2. CH1	2. ANODE
3. GND	3. BASE	3. ANODE 2	3. D2 (i)	3. Vp	3. CATHODE
4. V CC	4. EMITTER	4. CATHODE 2	4. D2 (c)	4. N/C	4. CATHODE
5. V EN	5. COLLECTOR	5. N/C	5. VBUS	5. CH2	5. CATHODE
6. V REF	6. COLLECTOR	6. CATHODE 1	6. D1 (c)	6. N/C	6. CATHODE
STYLE 25:	STYLE 26:	STYLE 27:	STYLE 28:	STYLE 29:	STYLE 30:
PIN 1. BASE 1	PIN 1. SOURCE 1	PIN 1. BASE 2	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. SOURCE 1
2. CATHODE	2. GATE 1	2. BASE 1	2. DRAIN	2. ANODE	2. DRAIN 2
3. COLLECTOR 2	3. DRAIN 2	3. COLLECTOR 1	3. GATE	3. COLLECTOR	3. DRAIN 2
4. BASE 2	4. SOURCE 2	4. EMITTER 1	4. SOURCE	4. EMITTER	4. SOURCE 2
5. EMITTER	5. GATE 2	5. EMITTER 2	5. DRAIN	5. BASE/ANODE	5. GATE 1
6. COLLECTOR 1	6. DRAIN 1	6. COLLECTOR 2	6. DRAIN	6. CATHODE	6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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